

TrenchT2™ Power MOSFET

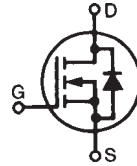
IXTH300N04T2

$$V_{DSS} = 40V$$

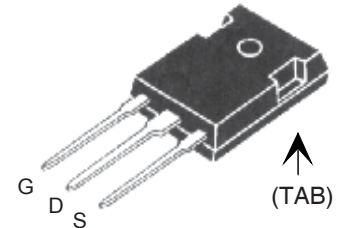
$$I_{D25} = 300A$$

$$R_{DS(on)} \leq 2.5m\Omega$$

N-Channel Enhancement Mode
Avalanche Rated



TO-247



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $175^\circ C$	40	V
V_{DGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$	40	V
V_{GSM}	Transient	± 20	V
I_{D25}	$T_C = 25^\circ C$	300	A
I_{LRMS}	Lead Current Limit, RMS	160	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	900	A
I_A	$T_C = 25^\circ C$	100	A
E_{AS}	$T_C = 25^\circ C$	600	mJ
P_D	$T_C = 25^\circ C$	480	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	1.6mm (0.062in.) from case for 10s	300	$^\circ C$
T_{sold}	Plastic body for 10 seconds	260	$^\circ C$
M_d	Mounting torque	1.13 / 10	Nm/lb.in.
Weight		6	g

Features

- International standard package
- $175^\circ C$ Operating Temperature
- High current handling capability
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Synchronous Buck Converters
- High Current Switching Power Supplies
- Battery Powered Electric Motors
- Resonant-mode power supplies
- Electronics Ballast Application
- Class D Audio Amplifiers

Symbol	Test Conditions ($T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	40		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0V$ $T_J = 150^\circ C$			150 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 50A$, Notes 1, 2			2.5 $m\Omega$

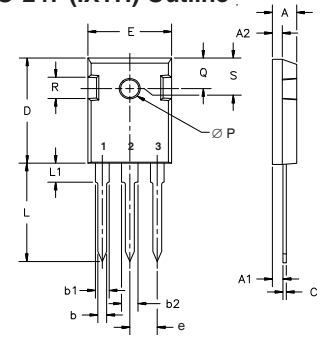
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}, I_D = 60\text{A}$, Note 1	55	94	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		10.7	nF
C_{oss}			1630	pF
C_{rss}			263	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 100\text{A}$ $R_G = 2\Omega$ (External)		22	ns
t_r			17	ns
$t_{d(off)}$			32	ns
t_f			13	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		145	nC
Q_{gs}			44	nC
Q_{gd}			36	nC
R_{thJC}			0.31	$^\circ\text{C/W}$
R_{thCH}		0.21		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			300 A
I_{SM}	Repetitive, Pulse width limited by T_{JM}			1000 A
V_{SD}	$I_F = 100\text{A}, V_{GS} = 0\text{V}$, Note 1			1.3 V
t_{rr}	$I_F = 150\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 20\text{V}$		53	ns
I_{RM}			1.8	A
Q_{RM}			47.7	nC

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

TO-247 (IXTH) Outline



Terminals: 1 - Gate 2 - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ 25°C

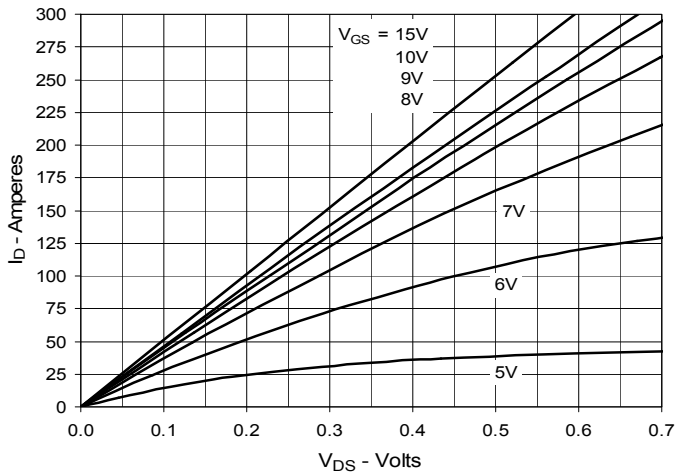


Fig. 2. Extended Output Characteristics @ 25°C

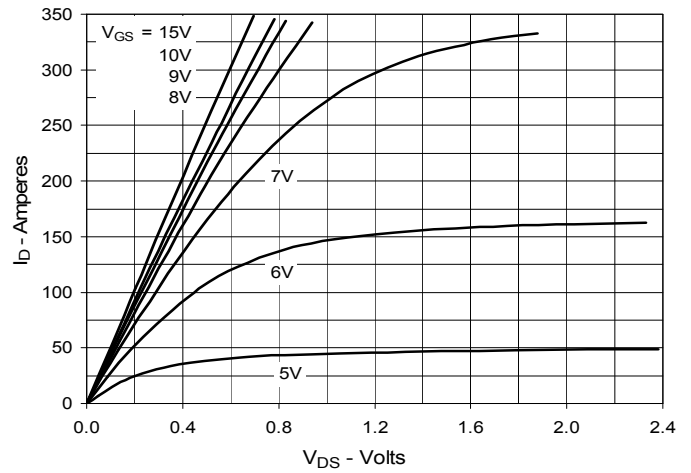


Fig. 3. Output Characteristics @ 150°C

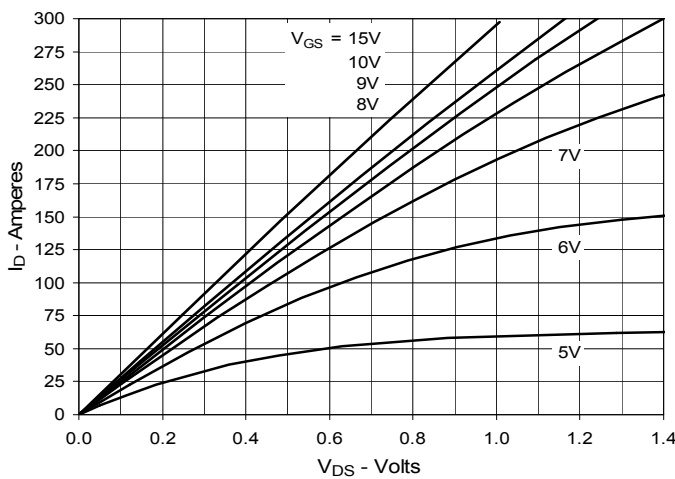


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 150A$ Value vs. Junction Temperature

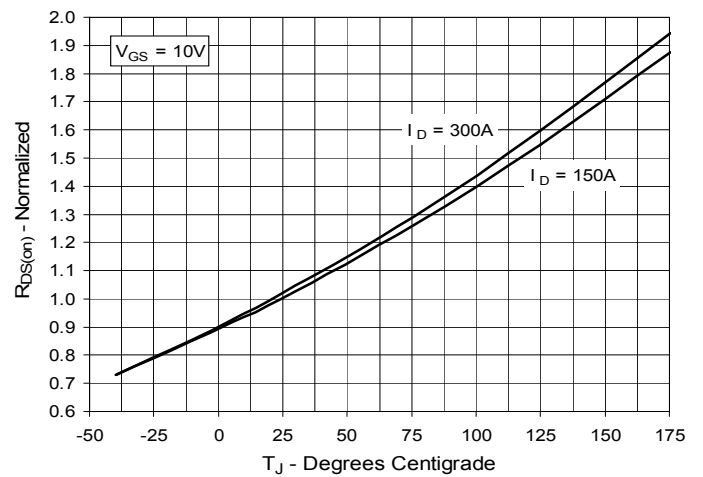


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 150A$ Value vs. Drain Current

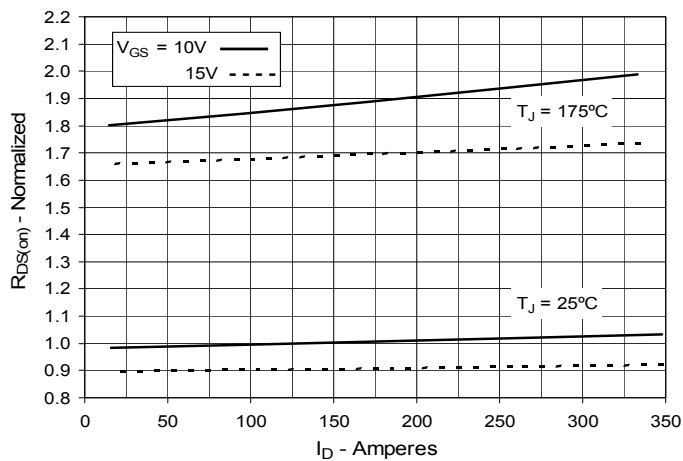


Fig. 6. Drain Current vs. Case Temperature

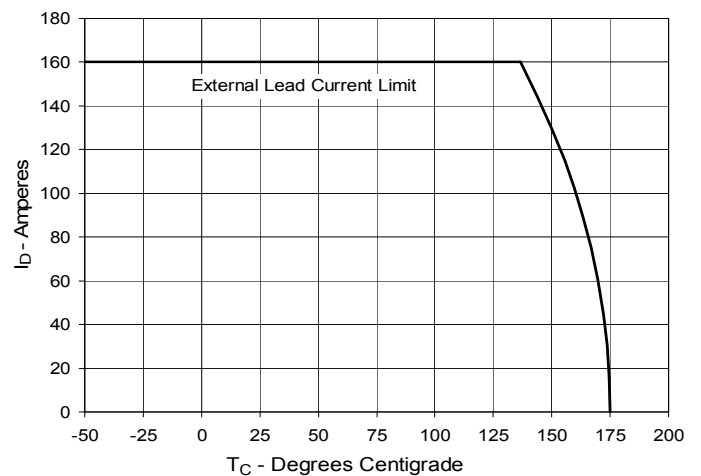


Fig. 7. Input Admittance

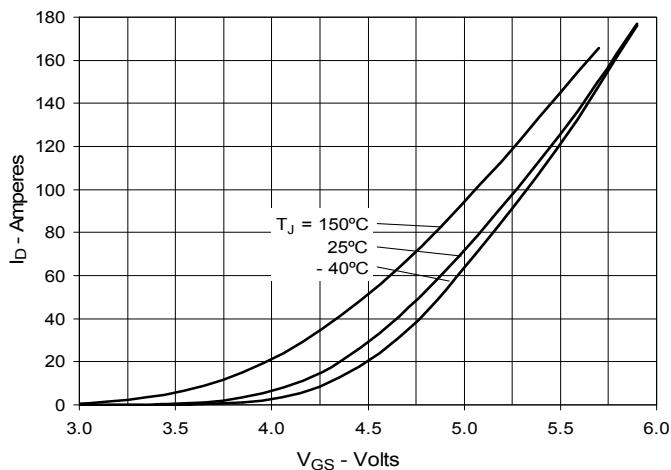


Fig. 8. Transconductance

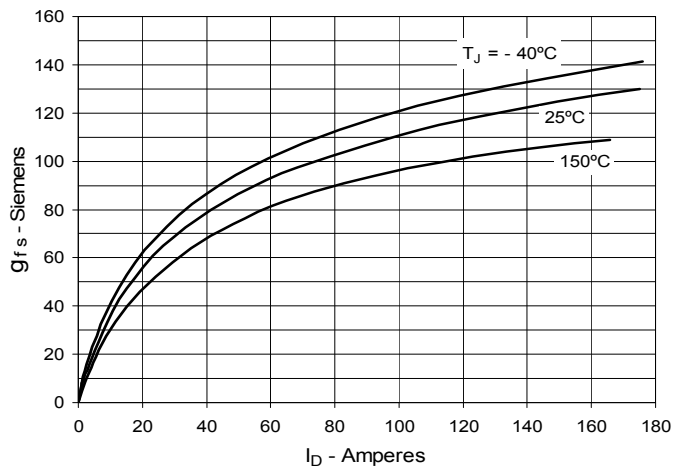


Fig. 9. Forward Voltage Drop of Intrinsic Diode

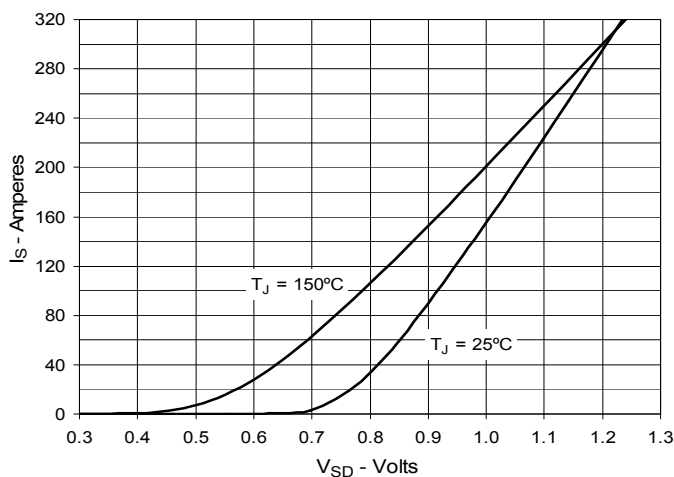


Fig. 10. Gate Charge

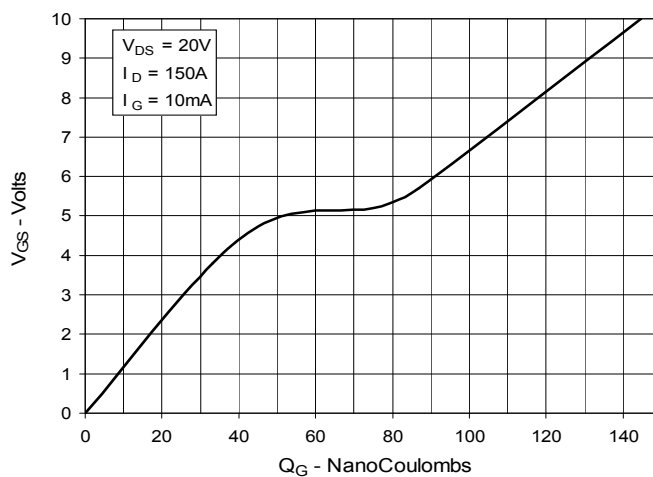


Fig. 11. Capacitance

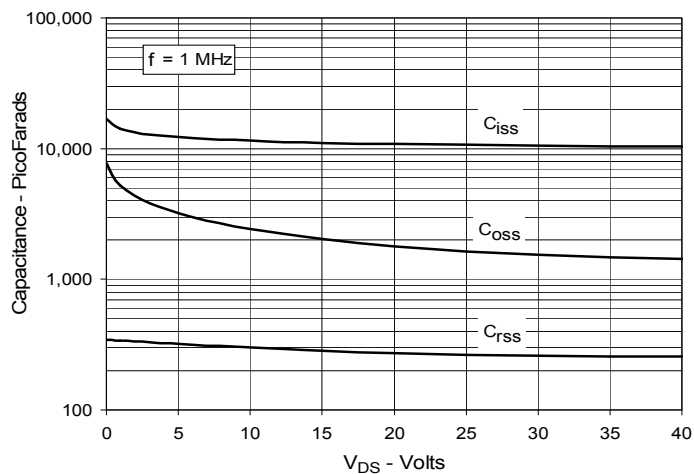
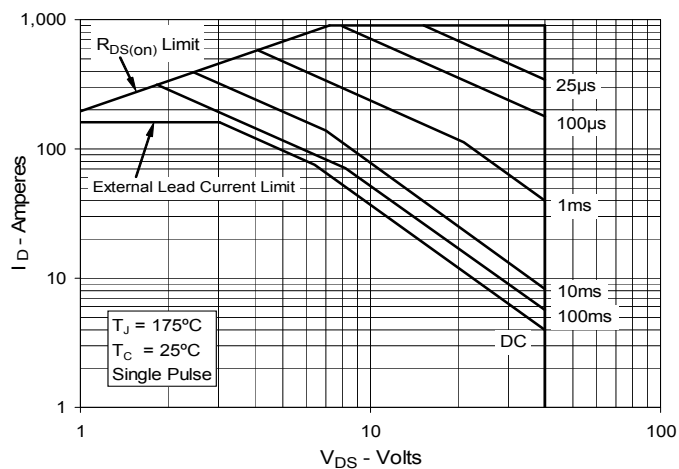


Fig. 12. Forward-Bias Safe Operating Area



IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

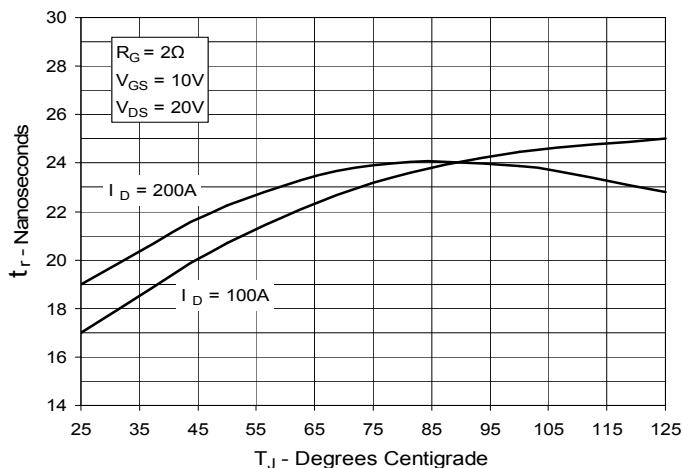


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

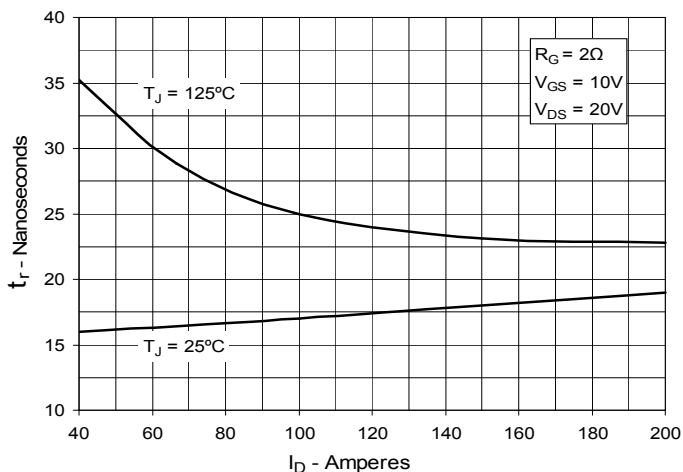


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

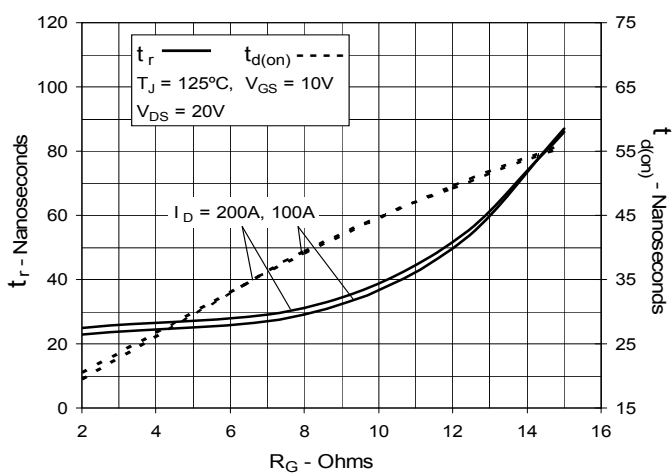


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

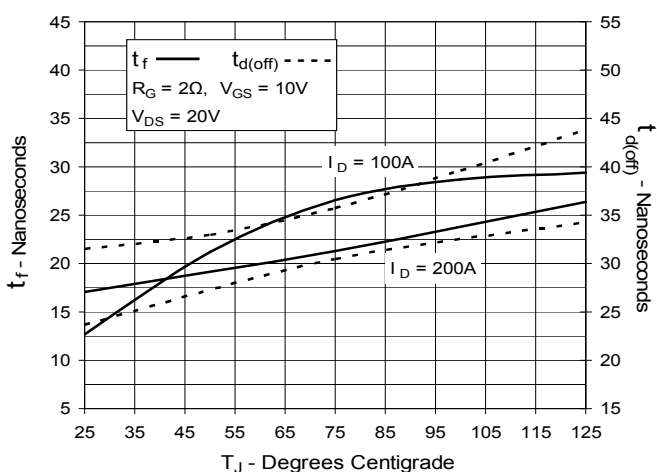


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

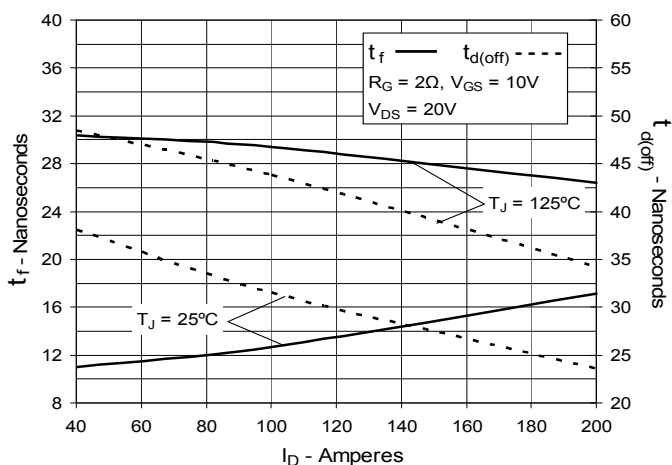


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

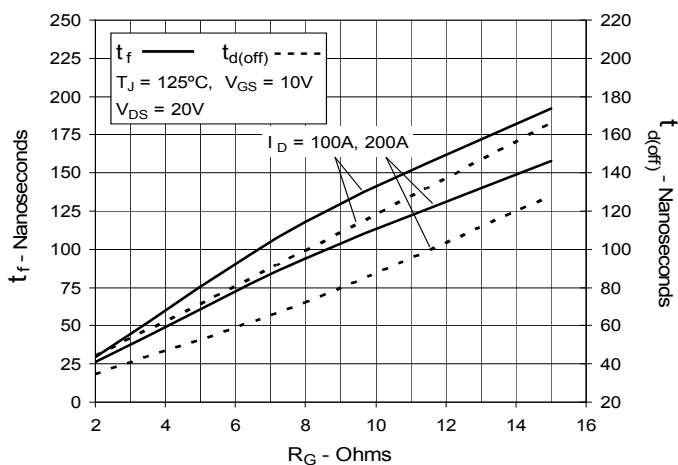


Fig. 19. Maximum Transient Thermal Impedance

